

**Notice of References Cited**

Application/Control No.

10/521,227

Applicant(s)/Patent Under

Reexamination

DAY, IAN EDWARD

Examiner

Eric Wong

Art Unit

2883

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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